IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

First Named Inventor: Mervyn John Rose	Confirmation No.: 7787
Application No.: 10/773,696	Patent No.: 7,592,191 B2
Filing Date: February 6, 2004	Patent Date: September 22, 2009
For: FIELD EMISSION BACKPLATE	Attorney Docket No.: 85170-5100

REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 C.F.R. § 1.323

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

It is requested that a Certificate of Correction be issued in connection with the above-identified patent correcting the errors listed on the accompanying Form PTO-1050. The corrections requested are as follows.

Title Page, Item (56) **References Cited**, FOREIGN PATENT DOCUMENTS, change "WO EP 0 578 428 1/1994" to - - EP EP 0 578 428 1/1994 - -. This change is requested to correct a typographical error.

Column 12, line 6 (claim 34, line 3), change "composing:" to - - comprising: - -. Support for this change appears in application claim 65.

This request is being made pursuant to 37 C.F.R. § 1.323 to correct errors of a clerical or typographical nature and do not involve changes that would constitute new matter or require reexamination. A fee of $100 is believed to be due for this request. Please charge the required fees to Winston & Strawn LLP Deposit Account No. 50-1814. Please issue a Certificate of Correction in due course.

Respectfully submitted,

9/30/09
Date

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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,592,191 B2
APPLICATION NO. : 10/773,696
DATED: : September 22, 2009
INVENTOR(S) : Rose et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page:
Item (56) **References Cited**, FOREIGN PATENT DOCUMENTS, change "WO EP 0 578 428 1/1994" to - - EP EP 0 578 428 1/1994 - -.

Column 12:
Line 6 (claim 34, line 3), change "composing:" to - - comprising: - -

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U.S. PATENT DOCUMENTS

2005/0179366	A1*	8/2005	Rose et al.	313/503
2006/0240734	A1*	10/2006	Chen	445/50
2006/0246693	A1*	11/2006	Tanaka et al.	438/487
2007/0284991	A1*	12/2007	Egi et al.	313/479
2008/0042926	A1*	2/2008	Egi et al.	345/32
2008/0050851	A1*	2/2008	Tanaka et al.	438/29
2008/0074031	A1*	3/2008	Yan	313/496
2008/0135848	A1*	6/2008	Yamazaki et al.	257/66
2008/0165315	A1*	7/2008	Nishida et al.	349/137
2008/0182349	A1*	7/2008	Yamazaki et al.	438/29

FOREIGN PATENT DOCUMENTS

EP	1 047 095		10/2000
EP	1 094 485		4/2001
GB	2 378 569	A	2/2003
GB	2 378 570	A	2/2003
JP	7073800		3/1995
JP	7141984		6/1995
JP	2002110544		4/2002
WO	EP 0 578 428		1/1994
WO	WO 02/080215	A2	10/2002

EP

* cited by examiner

a transparent window, wherein electrons from the tips are emitted into the wide band-gap light emitting material.

27. The field emission device of claim **26**, wherein the wide bank-gap light emitting material is a light emitting polymer.

28. The field emission device of claim **26**, wherein the transparent window is a thin film transparent metal.

29. The field emission device of claim **26**, wherein one surface of the light emitting material is disposed on the plurality of tips of the field emission backplate and the transparent window is disposed on another surface of the light emitting material.

30. The field emission device of claim **22**, wherein the device is a display device.

31. The field emission device of claim **22**, wherein the tips of the field emission backplate are of a density of at least 100 per square micron.

32. A method of forming a field emission backplate according to claim **14**, the method comprising:

depositing a thin film of amorphous semiconductor based material upon a substrate;

locally laser crystallizing a plurality of areas of the thin film amorphous semiconductor based material by exposure to at least one pulse laser interference pattern; and

growing crystalline semiconductor based material upon each of the plurality of crystallized areas of thin film amorphous semiconductor based material.

33. The method of claim **32**, further comprising the steps of depositing the thin film of amorphous semiconductor based material by plasma enhanced chemical vapor deposition.

34. A method of crystallizing areas of thin film amorphous semiconductor based material for use in the field emission backplate of claim **14**, the method composing: comprising:

forming a laser interferometer by splitting and recombining a laser beam;

placing a thin film of amorphous semiconductor based material in the plane of the recombination of the laser beam;

locally crystallizing areas of the thin film of amorphous semiconductor based material by subjecting the thin film to at least one laser pulse wherein the crystallized areas generated in the thin film amorphous semiconductor based material correspond to the interference pattern of the laser.

35. The method of claim **34**, wherein for a backplate of amorphous semiconductor based material, wherein the semiconductor based material is hydrogenated amorphous silicon, the laser operates at a wavelength of around 532 nm to maximize absorption.

36. The method of claim **34**, wherein the laser is a Nd:YAG laser.

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